



# STP24NF10 STB24NF10

## N-CHANNEL 100V - 0.055Ω - 26A TO-220 / D<sup>2</sup>PAK LOW GATE CHARGE STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP24NF10	100 V	< 0.060 Ω	26 A
STB24NF10	100 V	< 0.060 Ω	26 A

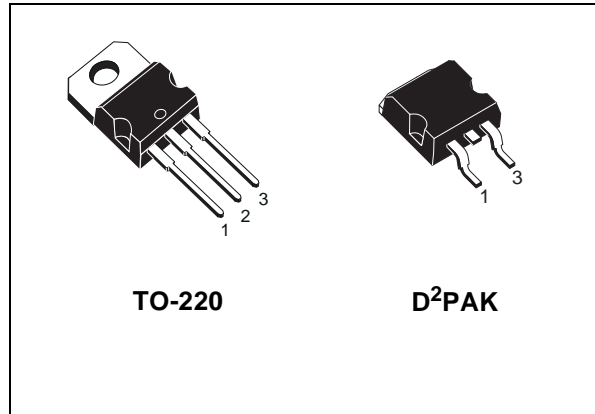
- TYPICAL R<sub>DS(on)</sub> = 0.055Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION

### DESCRIPTION

This Power Mosfet series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

### APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	100	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	100	V
V <sub>GS</sub>	Gate- source Voltage	±20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	26	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	18	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	104	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	85	W
	Derating Factor	0.57	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	9	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	220	mJ
T <sub>stg</sub>	Storage Temperature	- 55 to 175	°C
T <sub>j</sub>	Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 24A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.  
(2) Starting T<sub>j</sub> = 25°C, I<sub>D</sub> = 12A, V<sub>DD</sub> = 30V

## STP24NF10 - STB24NF10

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.76	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12 A		0.055	0.060	Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 15V, I <sub>D</sub> = 12 A		10		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		870		pF
C <sub>oss</sub>	Output Capacitance			125		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			50		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 50V, I_D = 12A$		60		ns
$t_r$	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		45		ns
$Q_g$	Total Gate Charge	$V_{DD} = 80V, I_D = 24A,$		30	41	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 10V$		6		nC
$Q_{gd}$	Gate-Drain Charge			10		nC

**SWITCHING OFF**

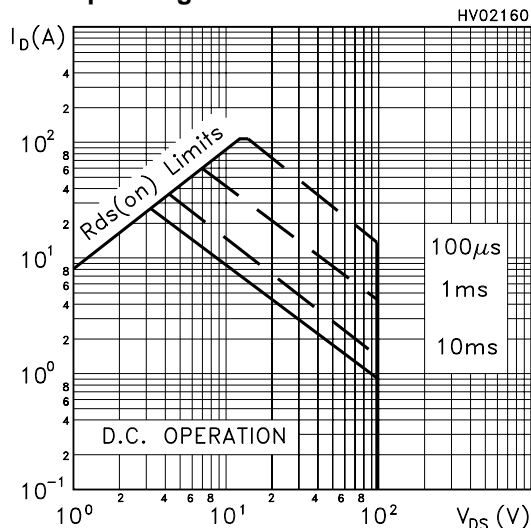
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 50V, I_D = 12A,$		50		ns
$t_f$	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		20		ns

**SOURCE DRAIN DIODE**

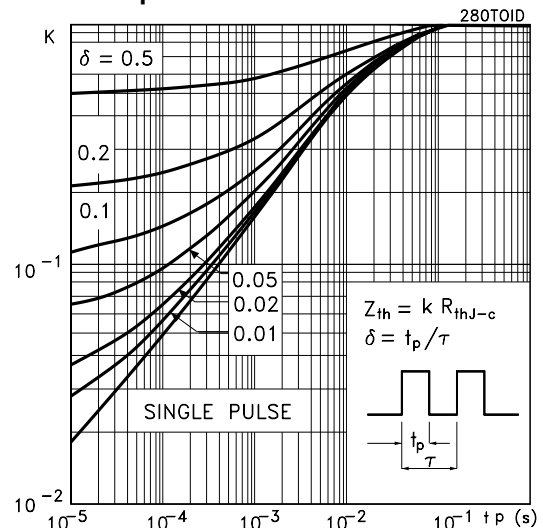
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				26	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				104	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 24A, V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 24A, di/dt = 100A/\mu s,$		100		ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 30V, T_j = 150^\circ C$		375		nC
$I_{RRM}$	Reverse Recovery Current	(see test circuit, Figure 5)		7.5		A

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
 2. Pulse width limited by safe operating area.

**Safe Operating Area**

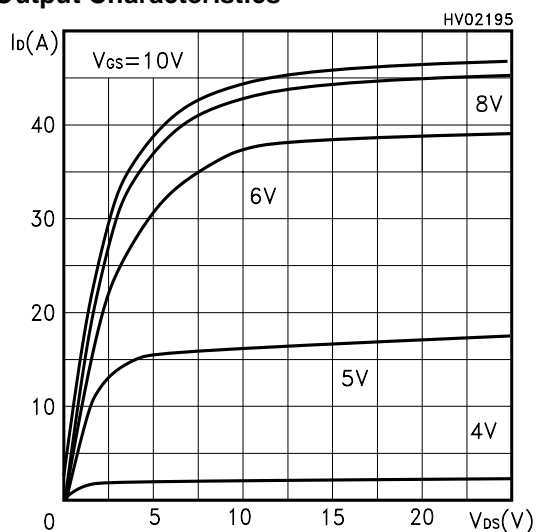


**Thermal Impedence**

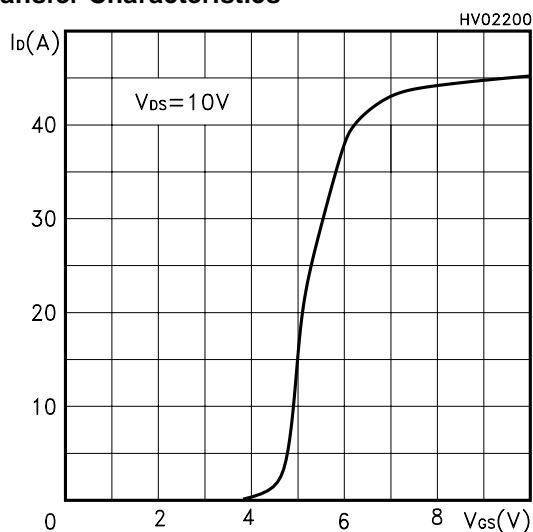


# STP24NF10 - STB24NF10

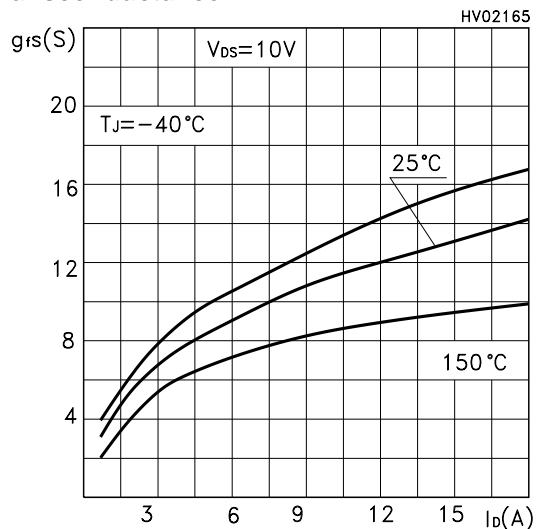
**Output Characteristics**



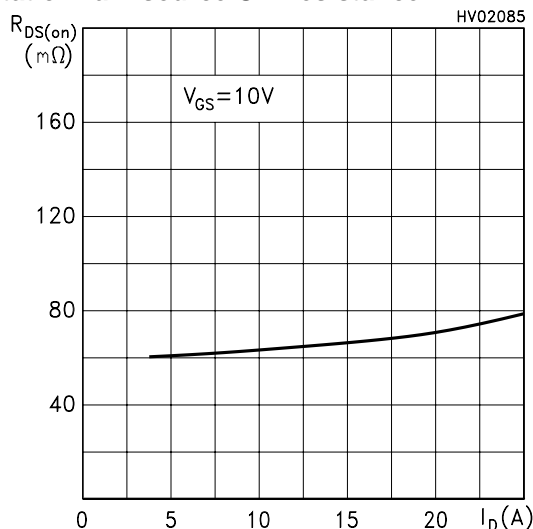
**Transfer Characteristics**



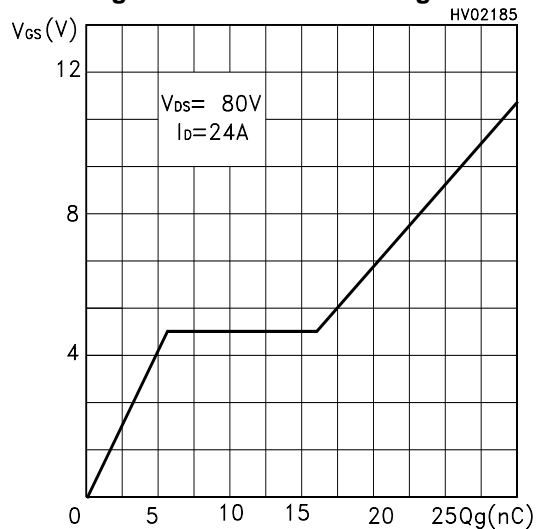
**Transconductance**



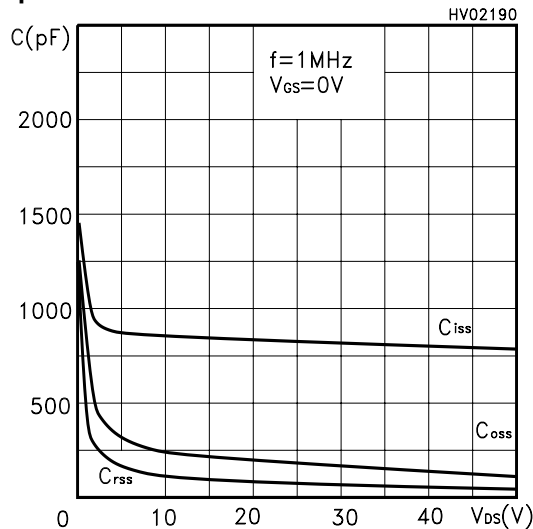
**Static Drain-source On Resistance**



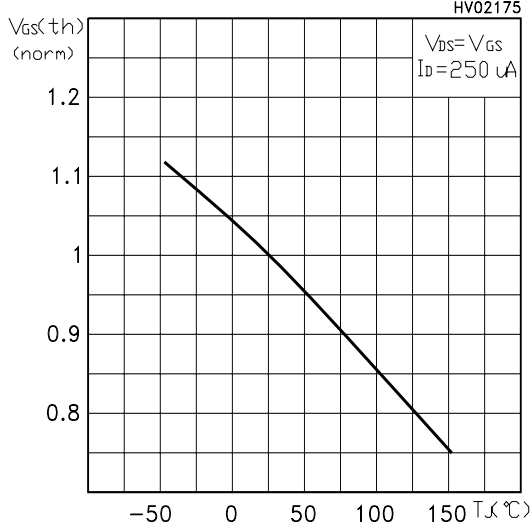
**Gate Charge vs Gate-source Voltage**



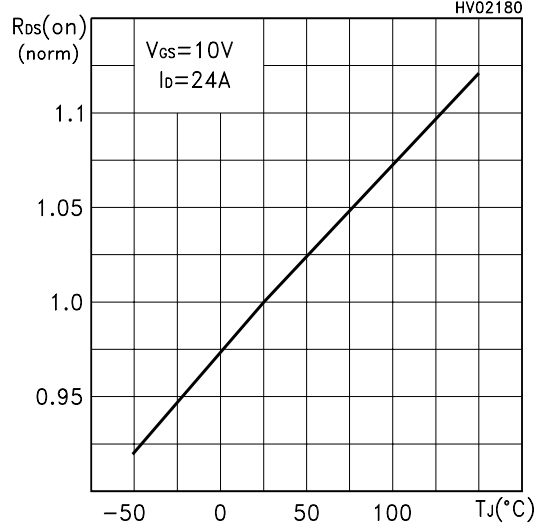
**Capacitance Variations**



Normalized Gate Threshold Voltage vs Temp. HV02175



Normalized On Resistance vs Temperature HV02180



Source-drain Diode Forward Characteristics HV02170

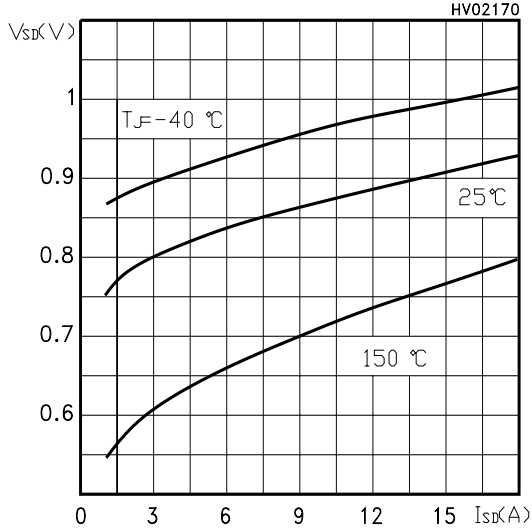


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform

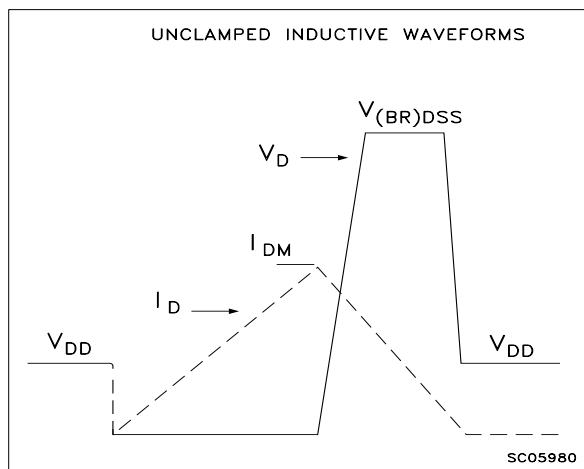


Fig. 3: Switching Times Test Circuit For Resistive Load

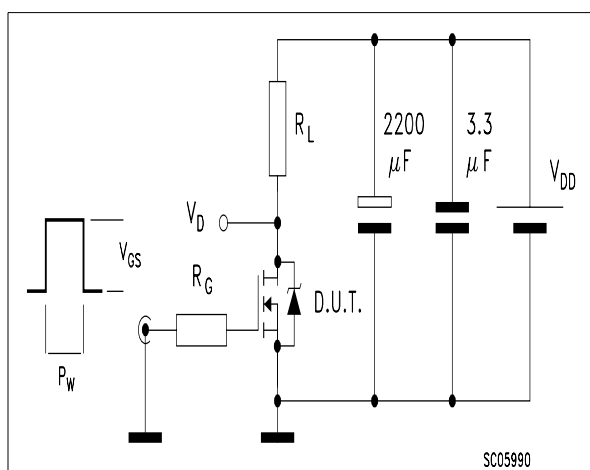


Fig. 4: Gate Charge test Circuit

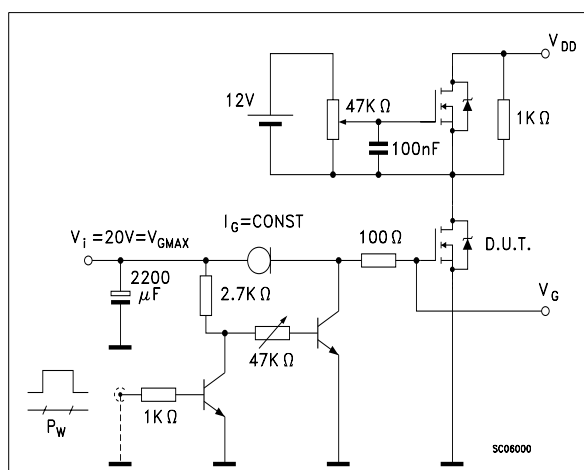
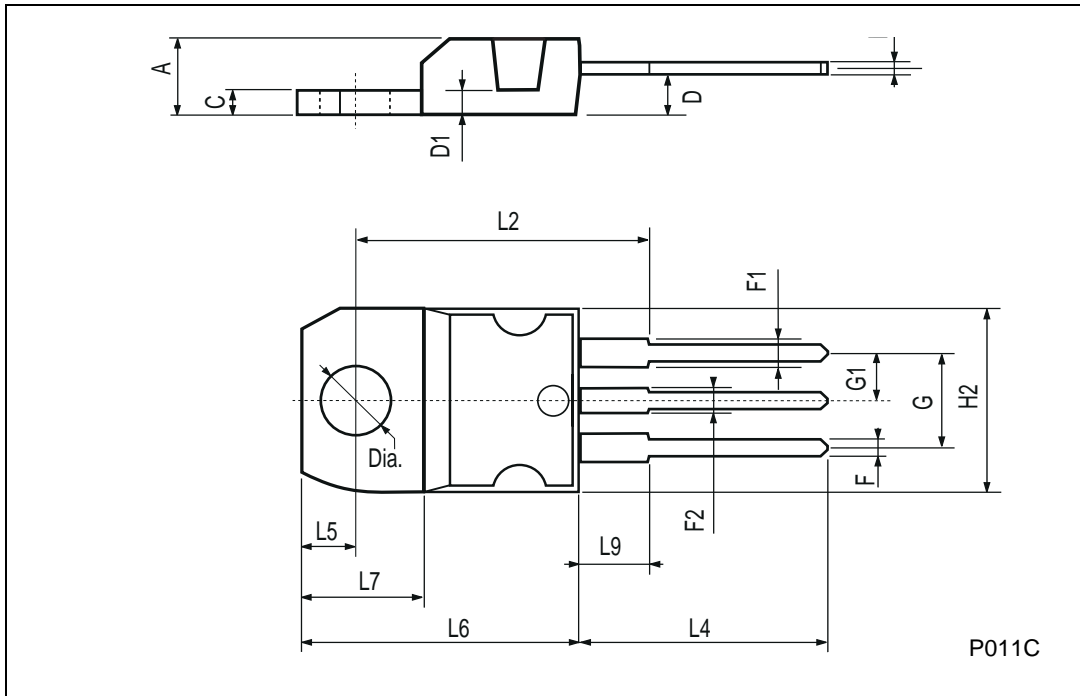


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



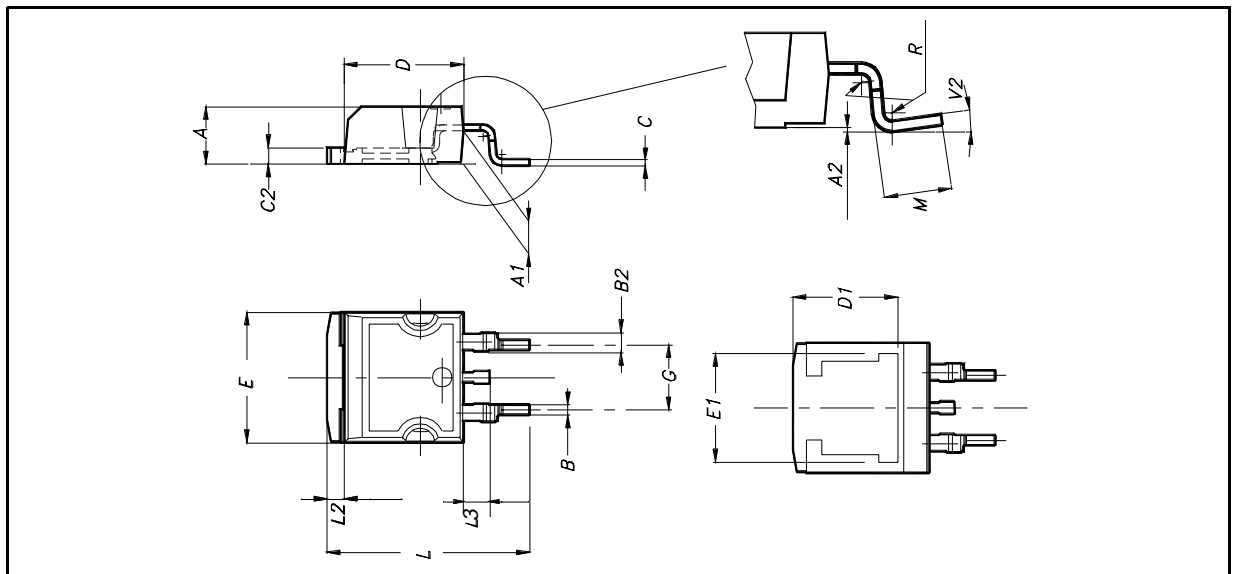
**TO-220 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



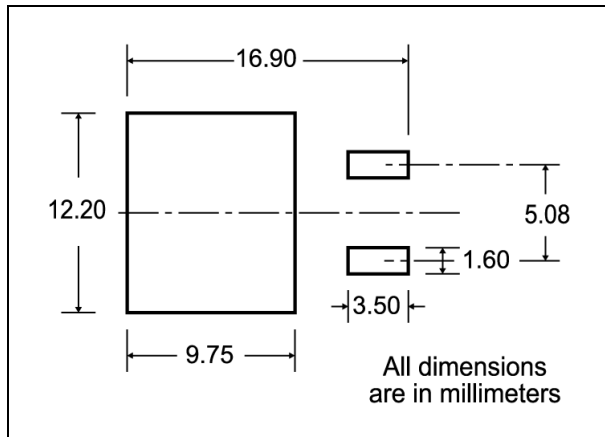
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			

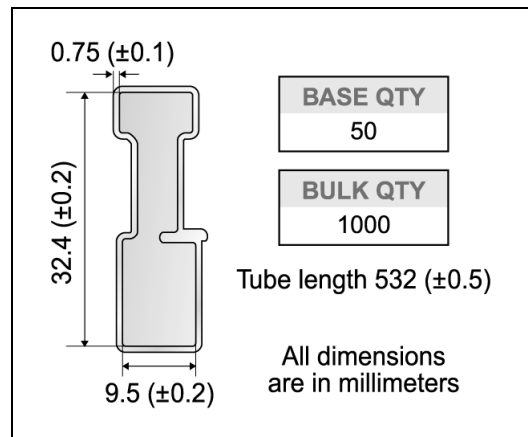




**D<sup>2</sup>PAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

\* on sales type



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